

Rev.A Dec.-2022

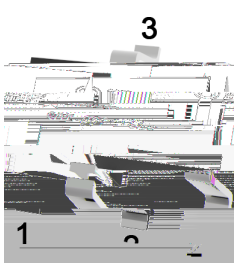
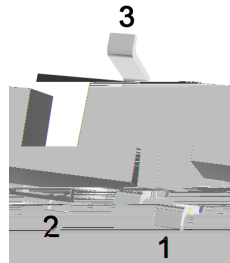
SOT-323

PNP

Silicon PNP Digital transistor in a SOT-323 Plastic Package.

With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing process, HF Product.

Switching, inverter circuit, interface circuit and driver circuit applications.



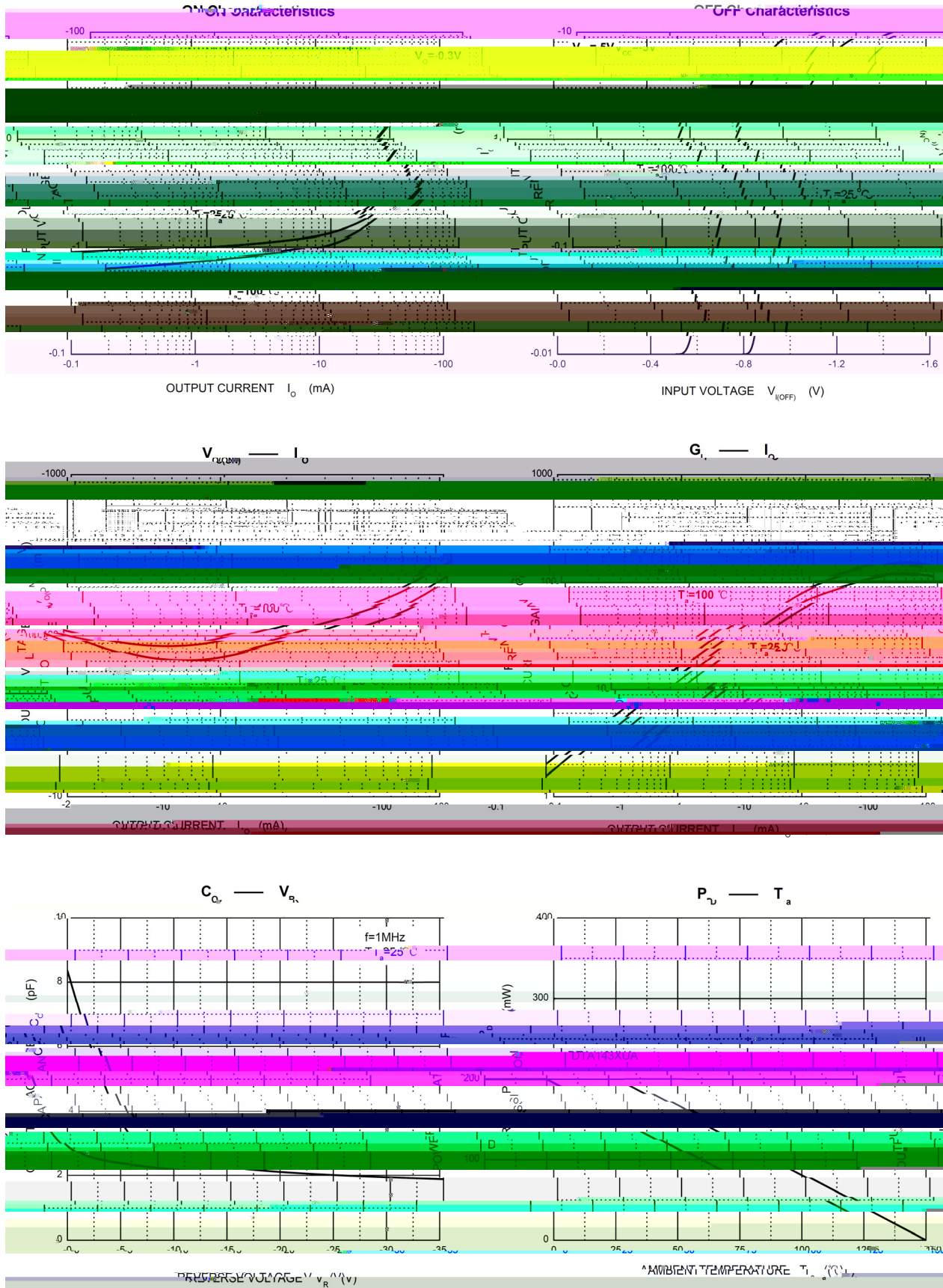
PIN 1 Base

PIN 2 Emitter

PIN 3 Collector

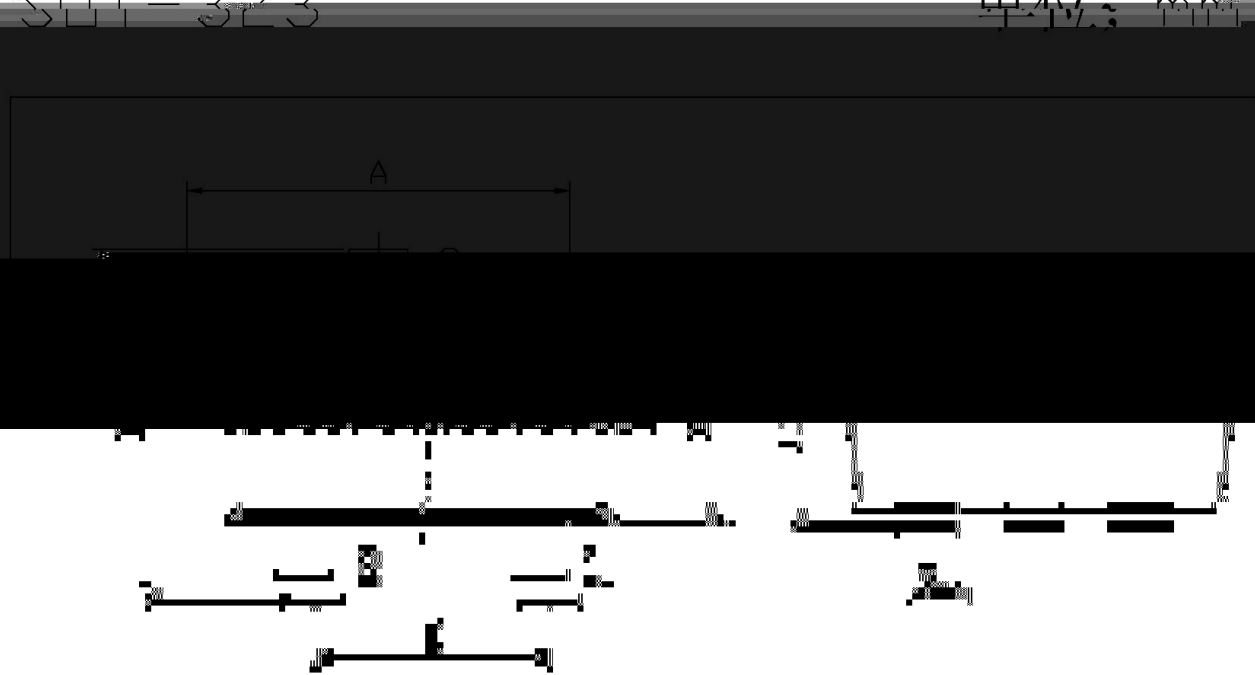
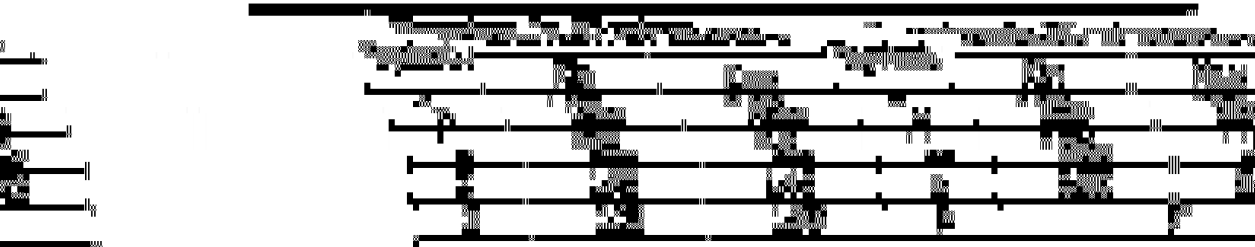
Parameter	Symbol	Rating	Unit
Supply Voltage	V_{CC}	-50	V
Input Voltage	V_{IN}	-20	V
		7.0	V
Output Current	I_O	-100	mA
Power Dissipation	P_D	200	mW
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55 150	

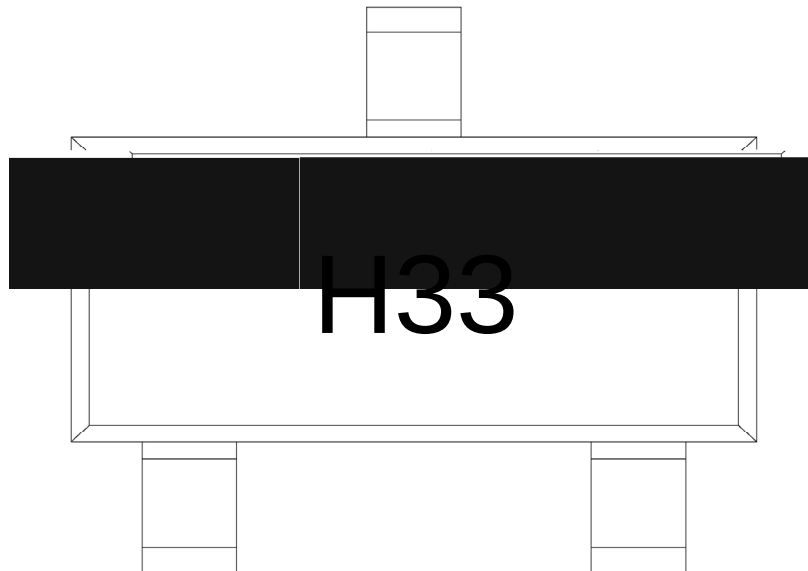
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Voltage	$V_{I(off)}$	$V_{CC}=-5.0V$ $I_O=-100\mu A$	-0.3			V
	$V_{I(on)}$	$V_O=-0.3V$ $I_O=-20mA$			-2.5	V
Output Voltage	$V_{O(on)}$	$I_O=-10mA$ $I_I=-0.5mA$		-0.1	-0.3	V
Input Current	I_I	$V_I=-5.0V$			-1.8	mA
Output current	$I_{O(off)}$	$V_{CC}=-50V$ $V_I=0V$			-0.5	μA
DC Current Gain	G_I	$V_O=-5.0V$ $I_O=-10mA$	30			
Transition Frequency	f_T	$V_O=-10V$ $I_O=-5.0mA$ $f=100MHz$		250		MHz
Resistance1	R_1		3.29	4.7	6.11	K Ω
Resistance Ratio	R_2/R_1		1.7	2.1	2.6	



SUT-323

单位: mm





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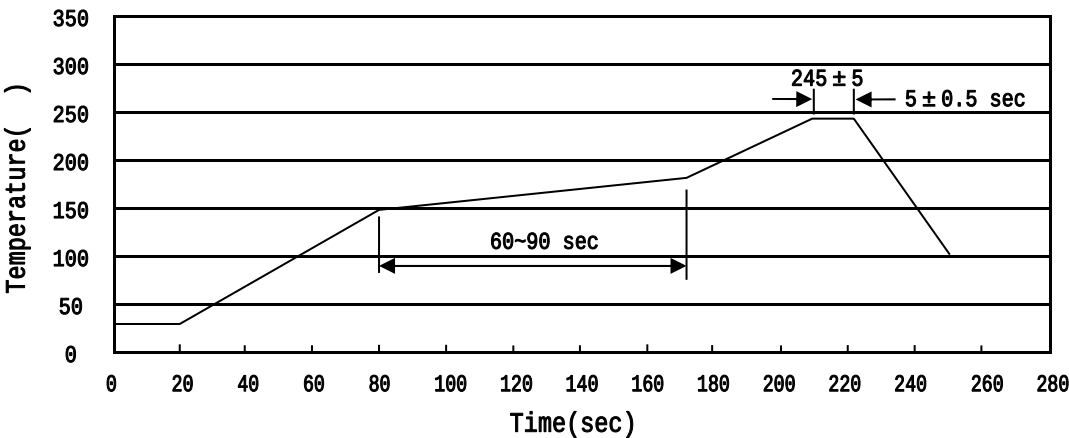
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Note:

H Company Code

33 Product Type Code

Wh p shrdwxrh Prr iioh i rr IU Uhi orw V r oghriq j +Pe-Frhh,



Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension		(unit mm ³)